Ordering number:EN2261A

PNP Epitaxial Planar Silicon Transistors

2SA1562

High-h_{FE} AF Amplifier Applications

Applications

· AF amplifier, various drivers.

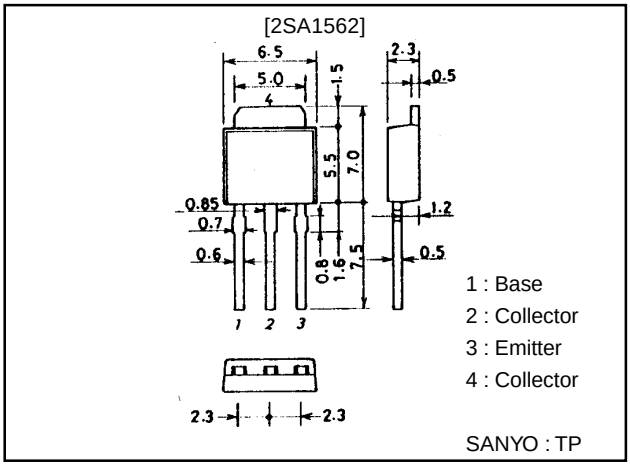
Features

· Adoption of MBIT process.
· High DC current gain.
· Large current capacity.
· Low collector-to-emitter saturation voltage.
· High V_{EBO}.

Package Dimensions

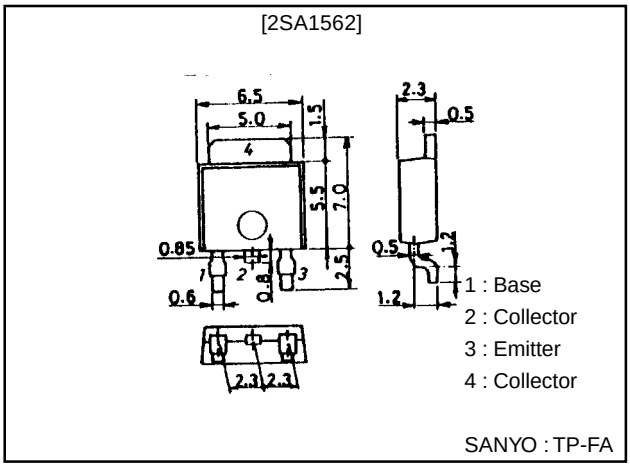
unit:mm

2045B



unit:mm

2044B



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		–30	V
Collector-to-Emitter Voltage	V_{CEO}		–25	V
Emitter-to-Base Voltage	V_{EBO}		–15	V
Collector Current	I_C		–1.2	A
Collector Current (Pulse)	I_{CP}		–2	A
Collector Dissipation	P_C		1	W
		Tc=25˚C	15	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

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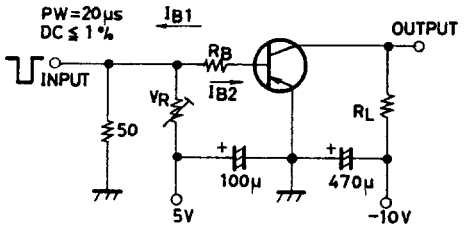
Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=–20V, I_E=0			–1	µA
Emitter Cutoff Current	I_{EBO}	V_{EB}=–10V, I_C=0			–1	µA
DC Current Gain	$h_{FE}1$	V_{CE}=–5V, I_C=–100mA	500	800	1200	
	$h_{FE}2$	V_{CE}=–5V, I_C=–10mA	350			
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=–50mA		130		MHz
Output Capacitance	C_{ob}	V_{CB}=–10V, f=1MHz		40		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=–500mA, I_B=–10mA		–0.1	–0.5	V
Base-to-Emitter Saturation Voltatage	$V_{BE(sat)}$	I_C=–500mA, I_B=–10mA		–0.78	–1.1	V
Collector-to-Base Breakdown Volage	$V_{(BR)CBO}$	I_C=(–)10A, I_E=0	–30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	–25			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10µA, I_C=0	–15			V
Turn-ON Time	t_{on}	See specified Test Circuit.		0.31		µs
Storage Time	t_{stg}	See specified Test Circuit.		0.88		µs
Fall Time	t_f	See specified Test Circuit.		0.23		µs

Switching Time Test Circuit



$-100\ I_{B1} = 100 I_{B2} = I_C = -700mA$

Unit (resistance :Ω, capacitance : F)